

Features :

- Isolated mounting base 2500V~
- Pressure contact technology with Increased power cycling capability
- Space and weight saving

Typical Applications

- AC/DC Motor drives
- Various rectifiers
- DC supply for PWM inverter

V_{DSM}, V_{RSM}	V_{DRM}, V_{RRM}	品名
900V	800V	Mx1000TH80W
1100V	1000V	Mx1000TH100W
1300V	1200V	Mx1000TH120W
1500V	1400V	Mx1000TH140W
1700V	1600V	Mx1000TH160W
1900V	1800V	Mx1000TH180W

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	$T_j(^{\circ}\text{C})$	VALUE			UNIT
				Min.	Typ.	Max.	
$I_{T(AV)}$	Mean on-state current	180° half sine wave 50Hz Single side cooled, $T_c=55^{\circ}\text{C}$	125			1000	A
$I_{T(RMS)}$	RMS on-state current					1570	A
I_{DRM} I_{RRM}	Repetitive peak current	at V_{DRM} at V_{RRM}	125			55	mA
I_{TSM}	Surge on-state current	10ms half sine wave, $V_R=0.6V_{RRM}$	125			26.0	kA
I^2t	I^2t for fusing coordination					3380	$\text{A}^2\text{s} \times 10^3$
V_{TO}	Threshold voltage		125			0.81	V
r_T	On-state slope resistance					0.21	$\text{m}\Omega$
V_{TM}	Peak on-state voltage			25		2.05	V
dv/dt	Critical rate of rise of off-state voltage	$V_{DM}=67\%V_{DRM}$	125			800	$\text{V}/\mu\text{s}$
di/dt	Critical rate of rise of on-state current	Gate source 1.5A $t_r \leq 0.5\mu\text{s}$ Repetitive	125			100	$\text{A}/\mu\text{s}$
I_{GT}	Gate trigger current	$V_A=12\text{V}$, $I_A=1\text{A}$	25	30		200	mA
V_{GT}	Gate trigger voltage			0.8		3.0	V
I_H	Holding current			10		200	mA
V_{GD}	Non-trigger gate voltage	$V_{DM}=67\%V_{DRM}$	125	0.2			V
$R_{th(j-c)}$	Thermal resistance Junction to case	D.C. Single side cooled per chip				0.052	$^{\circ}\text{C}/\text{W}$
$R_{th(c-h)}$	Thermal resistance case to heat sink	D.C. Single side cooled per chip				0.018	$^{\circ}\text{C}/\text{W}$
V_{iso}	Isolation voltage	50Hz,R.M.S., $t=1\text{min}$, $I_{iso}=1\text{mA}(\text{MAX})$		2500			V
F_m	Terminal connection torque(M12)				14.0		$\text{N}\cdot\text{m}$
	Mounting torque(M8)				12.0		$\text{N}\cdot\text{m}$
T_{vj}	Junction temperature			-40		125	$^{\circ}\text{C}$
T_{stg}	Stored temperature			-40		125	$^{\circ}\text{C}$
W_t	Weight				3460		g
Outline		M15					

Nips Thyristor/Diode Modules MD1000TH**W MR1000TH**W MC1000TH**W

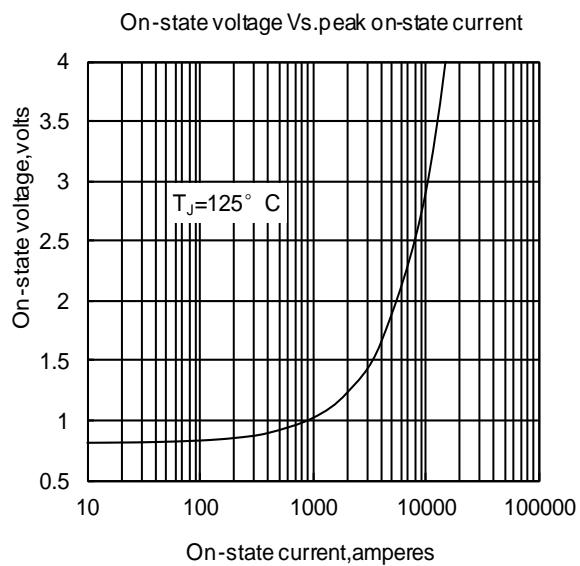


Fig1

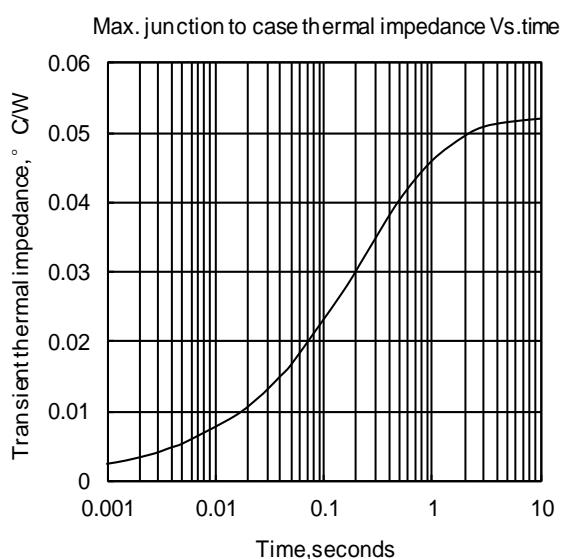


Fig2

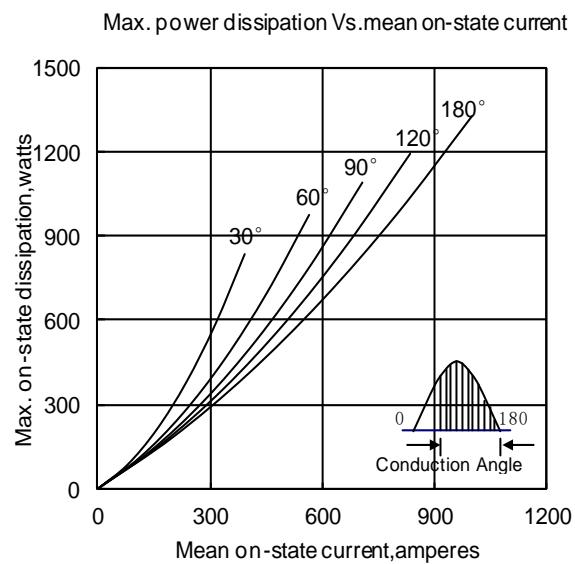


Fig3

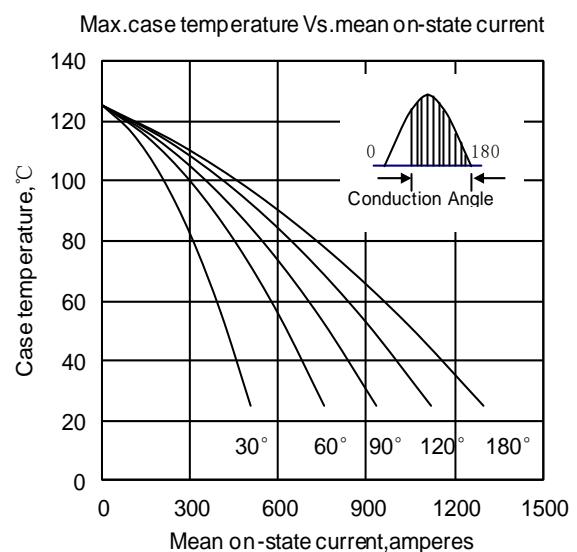


Fig4

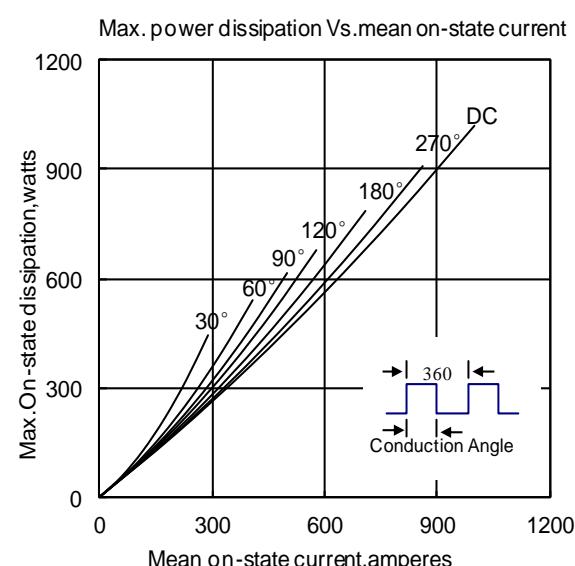


Fig5

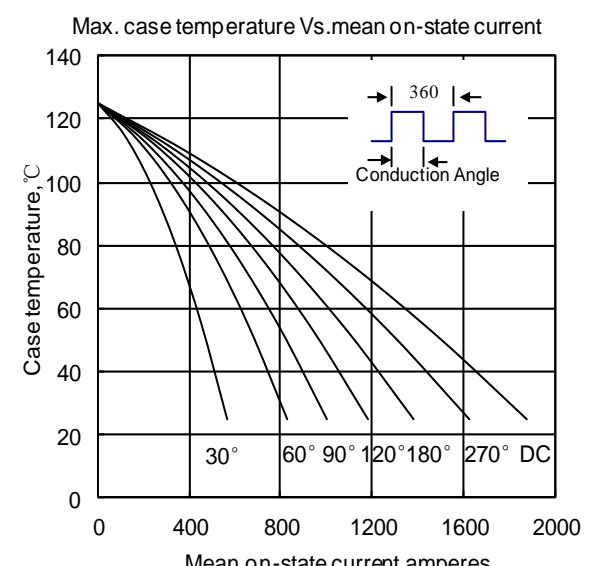


Fig6

NIPs Thyristor/Diode Modules MD1000TH**W MR1000TH**W MC1000TH**W

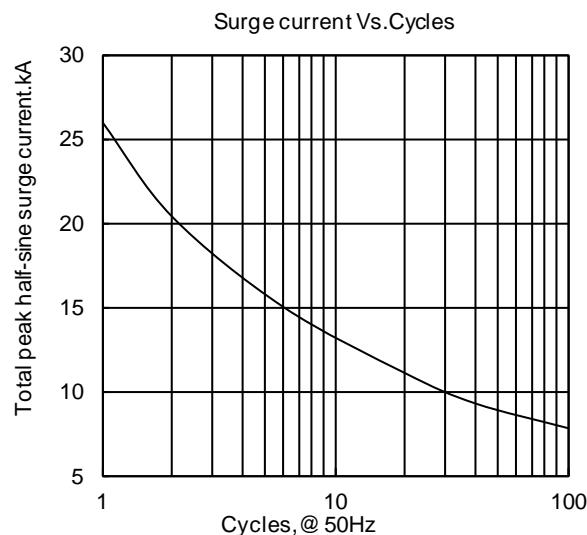


Fig7

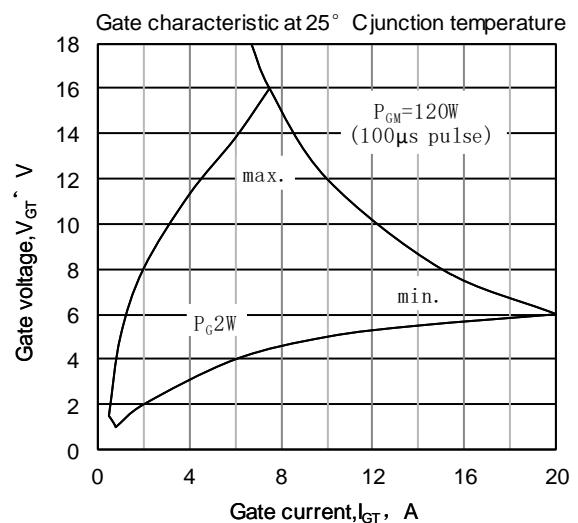


Fig8

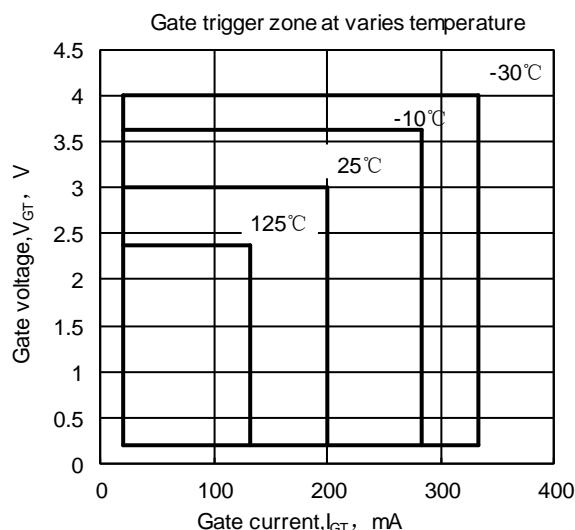
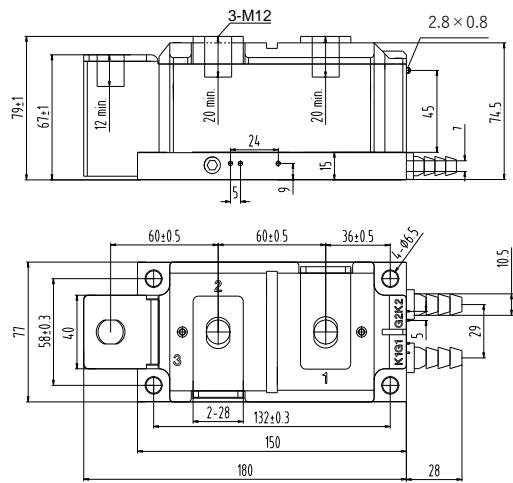


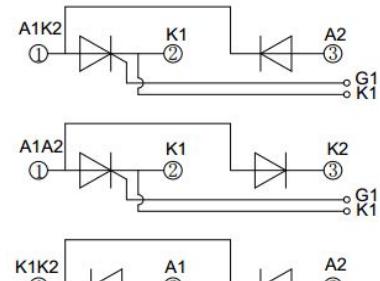
Fig9



MD1000TH**W

MR1000TH**W

MC1000TH**W



Unmarked dimensional tolerance : $\pm 0.5\text{mm}$